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REPLACEMENT CLAIMS

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1. (Amended) A semiconductor isolation structure comprising:

a substrate, the substrate comprising a surface;

a first device and a second device formed within the substrate;

an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:

a deep region which extends into the substrate, the deep region comprising a deep region cross-sectional area;

a single shallow region which extends to the surface of the substrate, the shallow region comprising:

a protective outer wall adjacent to the substrate;

an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall: and

the shallow region having a shallow region cross-sectional area;

wherein the deep region cross-sectional area is greater the shallow region cross-sectional area.

5. (Amended) A semiconductor isolation structure comprising:

a substrate, the substrate comprising a surface;

a first device and a second device formed within the substrate;

an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:

a deep region which extends into the substrate, the deep region comprising an oxide;

a single shallow region which extends to the surface of the substrate, the shallow region comprising:

a protective outer wall adjacent to the substrate,

an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall.

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a single deep region  
connected to a single  
shallow

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